

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	94	"silicon carbide" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 11:39
L2	32	"silicon carbide" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant". clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 11:40
L3	30	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant" and ("radio frequency" or "RF")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/11/22 14:22
L4	4	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant" and ("radio frequency" or "RF") and ammonia and electrode and field	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/11/22 14:24
L5	4	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant" and ("radio frequency" or "RF") and ammonia and electrode and field	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 14:30
L6	1	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant" and ("radio frequency" or "RF") and ammonia and electrode and field and (438/597,618,622,624.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 14:31
L7	1	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant" and ("radio frequency" or "RF") and ammonia and electrode and field and (438/597,618,622,624.ccls.)	US-PGPUB	OR	ON	2005/11/22 14:31
L8	0	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant" and ("radio frequency" or "RF") and ammonia and electrode and field and (438/597,618,622,624.ccls.).clm.	US-PGPUB	OR	ON	2005/11/22 14:31

S1	2486	"silicon carbide layer"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/15 10:36
S2	128	"silicon carbide layer" and (nitrogen with dope\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/15 10:37
S3	24	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/15 10:37
S4	12	"silicon carbide layer" and (nitrogen with dope\$4) and (leakage near4 current) and "dielectric constant"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/11/22 14:21
S5	2	("5800878").PN. or ((2001/0030369) or (2002/0027286) or (2001/0051445) or (2001/0031563)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/11/22 11:26
S6	0	(("5800878").PN. or ((2001/0030369) or (2002/0027286) or (2001/0051445) or (2001/0031563)).CCLS.) and silicon and carbon and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:02
S7	124	438/624.ccls. and silicon and carbon and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:02
S8	28	438/624.ccls. and silicon and carbon and nitrogen and "inert gas"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:02
S9	4	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:03
S10	4	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:03
S11	4	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy and RF	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:03
S12	4	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy and RF and power	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:04

S13	2	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy and RF and power and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:04
S14	2	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy and RF and power and electrode and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:04
S15	1	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy and RF and power and electrode and plasma and "silicon carbide"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:04
S16	1	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and energy and RF and power and electrode and plasma and "silicon carbide"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:13
S17	4	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and reaction	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/14 13:14
S18	4	438/624.ccls. and silicon and carbon and nitrogen and "inert gas" and (electric with field) and reaction and RF	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:06
S19	4881025	2004/0161535 A1	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:07
S20	51906	2004/0161535 A1 and ammonia	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:15
S21	0	"2004/0161535 A1" and ammonia	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:13
S22	0	"2004/0161535 A1" and flow	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:13
S23	0	"2004/0161535 A1"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:15

S24	0	"US 2004/0161535 A1"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:15
S25	0	(2004/0161535A1).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:16
S26	0	(2004/0161535A1).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:16
S27	0	(2004/0161535A1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:18
S28	0	(10/414467).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:19
S29	1	10/414467	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/07/06 12:19